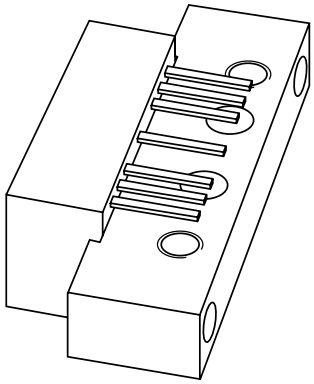
DATA SHEET



BGD802
860 MHz, 18.5 dB gain power doubler amplifier

Product specification
Supersedes data of 2001 Oct 30

2002 Jan 23

Philips Semiconductors

PHILIPS

860 MHz, 18.5 dB gain power doubler amplifier BGD802

FEATURES

- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

APPLICATIONS

- CATV systems operating in the 40 to 860 MHz frequency range.

DESCRIPTION

Hybrid amplifier module in a SOT115J package operating at a supply voltage of 24 V (DC).

PINNING - SOT115J

PIN	DESCRIPTION
1	input
2, 3	common
5	$+V_B$
7, 8	common
9	output

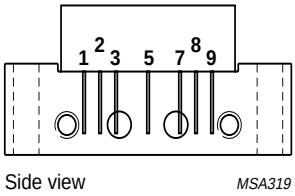


Fig.1 Simplified outline.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G_p	power gain	f = 50 MHz	18	19	dB
		f = 860 MHz	18.5	–	dB
I_{tot}	total current consumption (DC)	V_B = 24 V	–	410	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_B	supply voltage	–	25	V
V_i	RF input voltage	–	65	dBmV
T_{stg}	storage temperature	–40	+100	°C
T_{mb}	operating mounting base temperature	–20	+100	°C

CHARACTERISTICS

Table 1 Bandwidth 40 to 860 MHz; V_B = 24 V; T_{case} = 35 °C; $Z_S = Z_L$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz	18	18.5	19	dB
		f = 860 MHz	18.5	19.5	–	dB
SL	slope cable equivalent	f = 40 to 860 MHz	0.2	1.1	2	dB
FL	flatness of frequency response	f = 40 to 860 MHz	–	±0.2	±0.5	dB
s_{11}	input return losses	f = 40 to 80 MHz	20	35	–	dB
		f = 80 to 160 MHz	18.5	31	–	dB
		f = 160 to 320 MHz	17	27	–	dB
		f = 320 to 640 MHz	15.5	22	–	dB
		f = 640 to 860 MHz	14	20	–	dB
s_{22}	output return losses	f = 40 to 80 MHz	20	29.5	–	dB
		f = 80 to 160 MHz	18.5	29	–	dB
		f = 160 to 320 MHz	17	25.5	–	dB
		f = 320 to 640 MHz	15.5	23	–	dB
		f = 640 to 860 MHz	14	22	–	dB
s_{21}	phase response	f = 50 MHz	–45	–	+45	deg
CTB	composite triple beat	49 channels flat; V_o = 47 dBmV; measured at 859.25 MHz	–	–66	–63	dB
X_{mod}	cross modulation	49 channels flat; V_o = 47 dBmV; measured at 55.25 MHz	–	–65	–62	dB
CSO	composite second order distortion	49 channels flat; V_o = 47 dBmV; measured at 860.5 MHz	–	–67.5	–60	dB
d_2	second order distortion	note 1	–	–75	–69	dB
V_o	output voltage	d_{im} = –60 dB; note 2	61.5	63.5	–	dBmV
NF	noise figure	f = 50 MHz	–	4.5	5.5	dB
		f = 550 MHz	–	–	6	dB
		f = 650 MHz	–	–	7	dB
		f = 750 MHz	–	–	7.5	dB
		f = 860 MHz	–	6.5	9	dB
I_{tot}	total current consumption (DC)	note 3	–	395	410	mA

Notes

1. f_p = 55.25 MHz; V_p = 44 dBmV;
   f_q = 805.25 MHz; V_q = 44 dBmV;
   measured at $f_p + f_q$ = 860.5 MHz.
2. Measured according to DIN45004B:
   f_p = 851.25 MHz; $V_p = V_o$;
   f_q = 858.25 MHz; $V_q = V_o$ –6 dB;
   f_r = 860.25 MHz; $V_r = V_o$ –6 dB;
   measured at $f_p + f_q - f_r$ = 849.25 MHz.
3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

Table 2 Bandwidth 40 to 860 MHz; V_B = 24 V; T_{case} = 30 °C; $Z_S = Z_L$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz	18	18.5	19	dB
		f = 860 MHz	18.5	19.5	–	dB
SL	slope cable equivalent	f = 40 to 860 MHz	0.2	1.1	2	dB
FL	flatness of frequency response	f = 40 to 860 MHz	–	±0.2	±0.5	dB
s_{11}	input return losses	f = 40 to 80 MHz	20	35	–	dB
		f = 80 to 160 MHz	18.5	31	–	dB
		f = 160 to 320 MHz	17	27	–	dB
		f = 320 to 640 MHz	15.5	22	–	dB
		f = 640 to 860 MHz	14	20	–	dB
s_{22}	output return losses	f = 40 to 80 MHz	20	29.5	–	dB
		f = 80 to 160 MHz	18.5	29	–	dB
		f = 160 to 320 MHz	17	25.5	–	dB
		f = 320 to 640 MHz	15.5	23	–	dB
		f = 640 to 860 MHz	14	22	–	dB
s_{21}	phase response	f = 50 MHz	–45	–	+45	deg
CTB	composite triple beat	129 channels flat; V_o = 44 dBmV; measured at 859.25 MHz	–	–56.5	–54	dB
X_{mod}	cross modulation	129 channels flat; V_o = 44 dBmV; measured at 55.25 MHz	–	–61	–59	dB
CSO	composite second order distortion	129 channels flat; V_o = 44 dBmV; measured at 860.5 MHz	–	–64.5	–56	dB
d_2	second order distortion	note 1	–	–75	–69	dB
V_o	output voltage	d_{im} = –60 dB; note 2	61.5	63	–	dBmV
NF	noise figure	see Table 1	–	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	395	410	mA

Notes

1. f_p = 55.25 MHz; V_p = 44 dBmV;
   f_q = 805.25 MHz; V_q = 44 dBmV;
   measured at $f_p + f_q$ = 860.5 MHz.
2. Measured according to DIN45004B:
   f_p = 851.25 MHz; $V_p = V_o$;
   f_q = 858.25 MHz; $V_q = V_o$ –6 dB;
   f_r = 860.25 MHz; $V_r = V_o$ –6 dB;
   measured at $f_p + f_q - f_r$ = 849.25 MHz.
3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

Table 3 Bandwidth 40 to 750 MHz; V_B = 24 V; T_{case} = 30 °C; $Z_S = Z_L$ = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz	18	18.5	19	dB
		f = 750 MHz	18.5	19.4	–	dB
SL	slope cable equivalent	f = 40 to 750 MHz	0.2	–	2	dB
FL	flatness of frequency response	f = 40 to 750 MHz	–	–	±0.5	dB
s_{11}	input return losses	f = 40 to 80 MHz	20	35	–	dB
		f = 80 to 160 MHz	18.5	31	–	dB
		f = 160 to 320 MHz	17	27	–	dB
		f = 320 to 640 MHz	15.5	22	–	dB
		f = 640 to 750 MHz	14	20	–	dB
s_{22}	output return losses	f = 40 to 80 MHz	20	29.5	–	dB
		f = 80 to 160 MHz	18.5	29	–	dB
		f = 160 to 320 MHz	17	25.5	–	dB
		f = 320 to 640 MHz	15.5	23	–	dB
		f = 640 to 750 MHz	14	22	–	dB
s_{21}	phase response	f = 50 MHz	–45	–	+45	deg
CTB	composite triple beat	110 channels flat; V_o = 44 dBmV; measured at 745.25 MHz	–	–60.5	–58	dB
X_{mod}	cross modulation	110 channels flat; V_o = 44 dBmV; measured at 55.25 MHz	–	–62.5	–60	dB
CSO	composite second order distortion	110 channels flat; V_o = 44 dBmV; measured at 746.5 MHz	–	–66	–60	dB
d_2	second order distortion	note 1	–	–	–72	dB
V_o	output voltage	d_{im} = –60 dB; note 2	64	–	–	dBmV
NF	noise figure	see Table 1	–	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	395	410	mA

Notes

1. f_p = 55.25 MHz; V_p = 44 dBmV;
   f_q = 691.25 MHz; V_q = 44 dBmV;
   measured at $f_p + f_q$ = 746.5 MHz.
2. Measured according to DIN45004B:
   f_p = 740.25 MHz; $V_p = V_o$;
   f_q = 747.25 MHz; $V_q = V_o$ –6 dB;
   f_r = 749.25 MHz; $V_r = V_o$ –6 dB;
   measured at $f_p + f_q - f_r$ = 738.25 MHz.
3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

Table 4 Bandwidth 40 to 550 MHz; V_B = 24 V; T_{case} = 30 °C; $Z_S = Z_L$ = 75 Ω

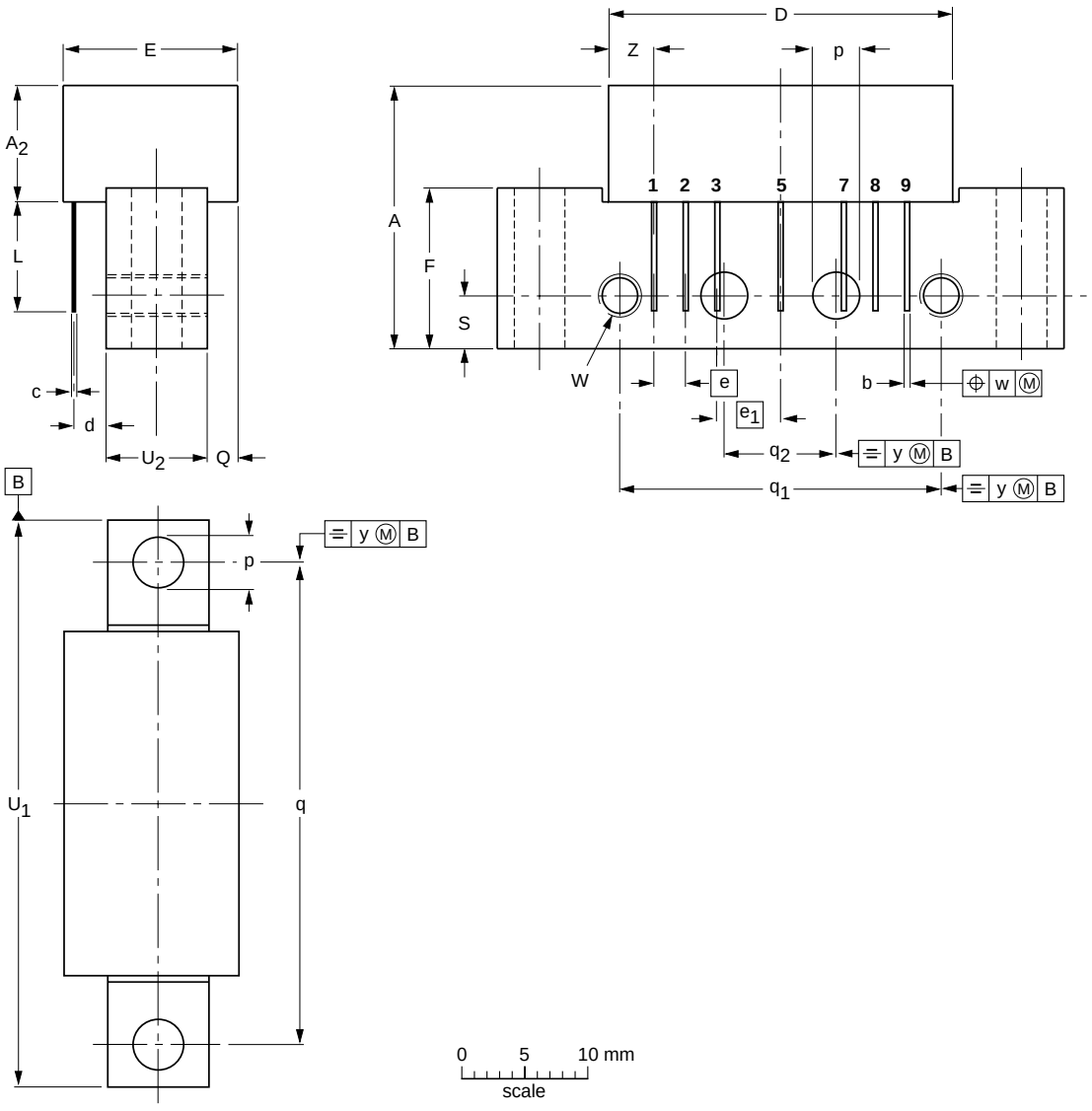
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	f = 50 MHz	18	18.5	19	dB
		f = 550 MHz	18.5	19.3	–	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0.2	–	2	dB
FL	flatness of frequency response	f = 40 to 550 MHz	–	–	±0.3	dB
s_{11}	input return losses	f = 40 to 80 MHz	20	35	–	dB
		f = 80 to 160 MHz	18.5	31	–	dB
		f = 160 to 320 MHz	17	27	–	dB
		f = 320 to 550 MHz	16	22	–	dB
s_{22}	input return losses	f = 40 to 80 MHz	20	29.5	–	dB
		f = 80 to 160 MHz	18.5	29	–	dB
		f = 160 to 320 MHz	17	25.5	–	dB
		f = 320 to 550 MHz	16	23	–	dB
s_{21}	phase response	f = 50 MHz	–45	–	+45	deg
CTB	composite triple beat	77 channels flat; V_o = 44 dBmV; measured at 547.25 MHz	–	–67	–65	dB
X_{mod}	cross modulation	77 channels flat; V_o = 44 dBmV; measured at 55.25 MHz	–	–66	–63	dB
CSO	composite second order distortion	77 channels flat; V_o = 44 dBmV; measured at 548.5 MHz	–	–67	–63	dB
d_2	second order distortion	note 1	–	–	–72	dB
V_o	output voltage	d_{im} = –60 dB; note 2	65	–	–	dBmV
NF	noise figure	see Table 1	–	–	–	dB
I_{tot}	total current consumption (DC)	note 3	–	395	410	mA

Notes

1. f_p = 55.25 MHz; V_p = 44 dBmV;
   f_q = 493.25 MHz; V_q = 44 dBmV;
   measured at $f_p + f_q$ = 548.5 MHz.
2. Measured according to DIN45004B:
   f_p = 540.25 MHz; $V_p = V_o$;
   f_q = 547.25 MHz; $V_q = V_o$ –6 dB;
   f_r = 549.25 MHz; $V_r = V_o$ –6 dB;
   measured at $f_p + f_q - f_r$ = 538.25 MHz.
3. The module normally operates at V_B = 24 V, but is able to withstand supply transients up to 30 V.

PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads **SOT115J**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_2 max.	b	c	D max.	d max.	E max.	e	e_1	F	L min.	p	Q max.	q	q_1	q_2	S	U_1 max.	U_2	W	w	y	Z max.
mm	20.8	9.1	0.51 0.38	0.25	27.2	2.54	13.75	2.54	5.08	12.7	8.8	4.15 3.85	2.4	38.1	25.4	10.2	4.2	44.75	8	6-32 UNC	0.25	0.1	3.8

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT115J						99-02-06

DATA SHEET STATUS

DATA SHEET STATUS[1]	PRODUCT STATUS[2]	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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CAUTION
This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

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